2026

ICEMOS SUPERJUNCTION MOSFET
Product Qualification Reliability Test Report

ICES10N60D

Report Description
This report describes the characteristics of the product as it pertains to the device quality and reliability. The samples used for this qualification were taken from production lots that were manufactured and tested using our standard production processes and meet the device specifications.

The qualification test results of the product as outlined in this document are based on recognized industry standard reliability test methods.

Qualification Assessment
This product has successfully completed all qualification reliability testing to meet the recognized industry standards and is therefore granted “Full Qualification” status from 2025. This reliability report is subject to appropriate updates as required.

For additional information, please contact your IceMOS Sales Representative. (www.icemostech.com).

ISSUED BY: ICEMOS TECHNOLOGY

ICES10N60D Reliability Test Report

Product: ICES10N60D
Package: DPAK
MSL Level: MSL-3

Items	Test Description(Abbr.)	Test method.	Stress Condition	Sample Qty.	Electrical Reject	Result
1	Pre-conditioning (**MSL3**)	JESD22-020D	Bake : 125C, 24hrs Moisture Soak : 60C,60%RH,40hrs Reflow : 260C, 3times	77pcs*1lot	0/77	PASS
2	Temperature Cycle(**TCT**)	JESD22-A104	1000 cycles, Δ Tj -55 to 150˚C	77pcs*1lot	0/77	PASS
3	Steady State Gate Bias positive (**HTGB)**	Mil-Std. 750 Method 1042-B	1000 hrs, VGS = +24V Tj = 150˚C	80pcs*1lot	0/80	PASS
4	Steady State Gate Bias negative (**HTGB)**	Mil-Std. 750 Method 1042-B	1000 hrs, VGS = -24V Tj = 150˚C	80pcs*1lot	0/80	PASS
5	Steady State Reverse bias (**HTRB)**	Mil-Std. 750 Method 1042-A	1000 hrs, VDS = 480V Tj = 150˚C	77pcs*1lot	0/77	PASS
6	High Temp High Humidity Reverse Bias (**H3TRB**)	Mil-Std. 750 Method 1042-A	1000 hrs, VDS = 100V Tj = 85˚C, RH = 85%	75pcs*1lot	0/75	PASS